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Author and Subject Index
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The Computer-Derived 1972 Journal Index

The Publication Committee of the Society recommended the use of a computer-derived index in 1968, and this practice is planned to be continued. This index is published two months earlier than the usual index and makes possible indexing more information than before. These indices refer only to *Journal* articles and reviews and do not include information on meeting paper authors, titles, or subjects. These indices were prepared for the *Journal* by the Institute for Scientific Information, Philadelphia, Pennsylvania.

Using the Index

1. Given any author, go directly to his name in the author and title index to find the full paper title with a page citation or to find a cross-reference to a primary author.
2. Given any topic, go to the subject index and search for the key word itself.
3. For a detailed explanation of symbols and abbreviations, see the sample pages before the individual author and title index and the subject index.
4. Chemical formulae cannot be reproduced directly because the conventional computer printout appears in capital letters only. For example, BI3 could be three atoms of bismuth or boron triiodide. To avoid this ambiguity, to a large extent an attempt has been made to write out chemical formulae.
5. In the author index, an author is always listed with all available initials, which for lack of space sometimes can mean omission of one or two letters from the end of his last name.

The Publication Committee will appreciate comments on the usefulness and accuracy of this index.

NEWTON SCHWARTZ
Chairman
Publication Committee

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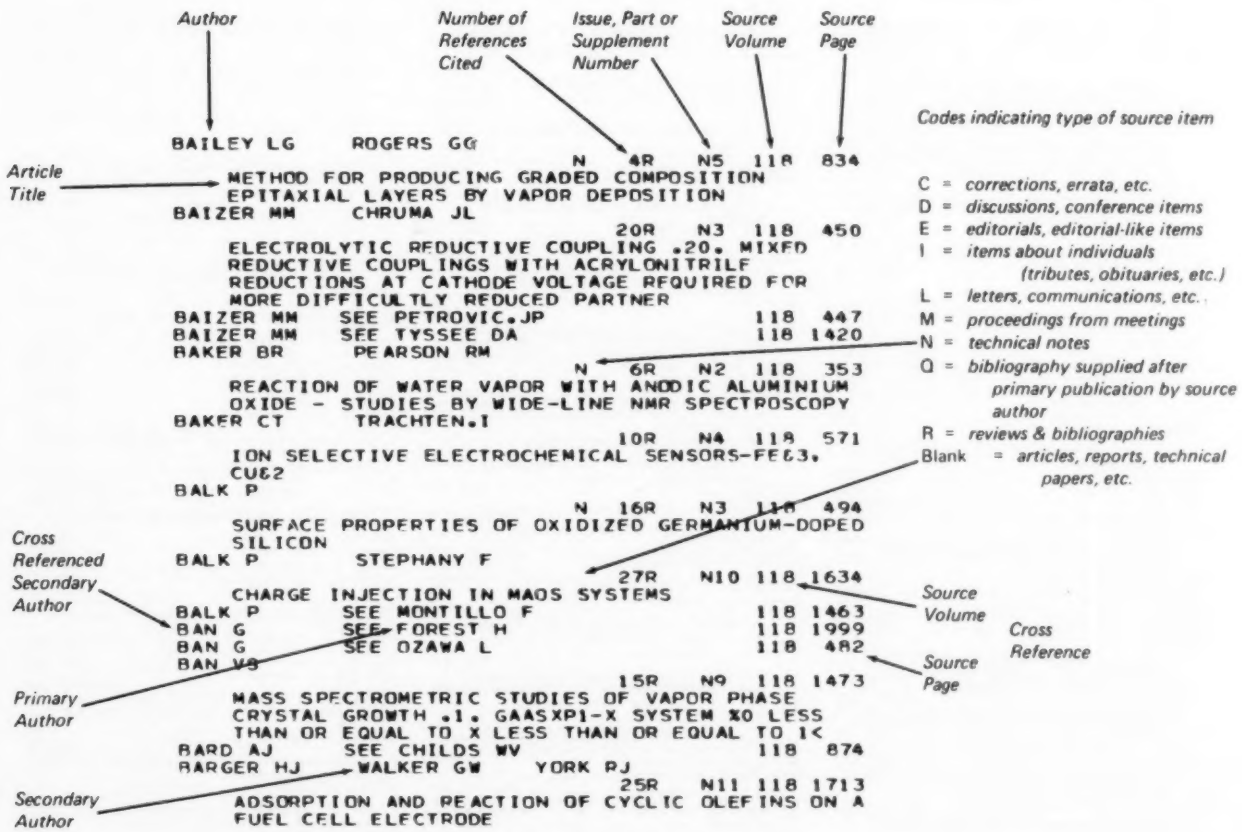
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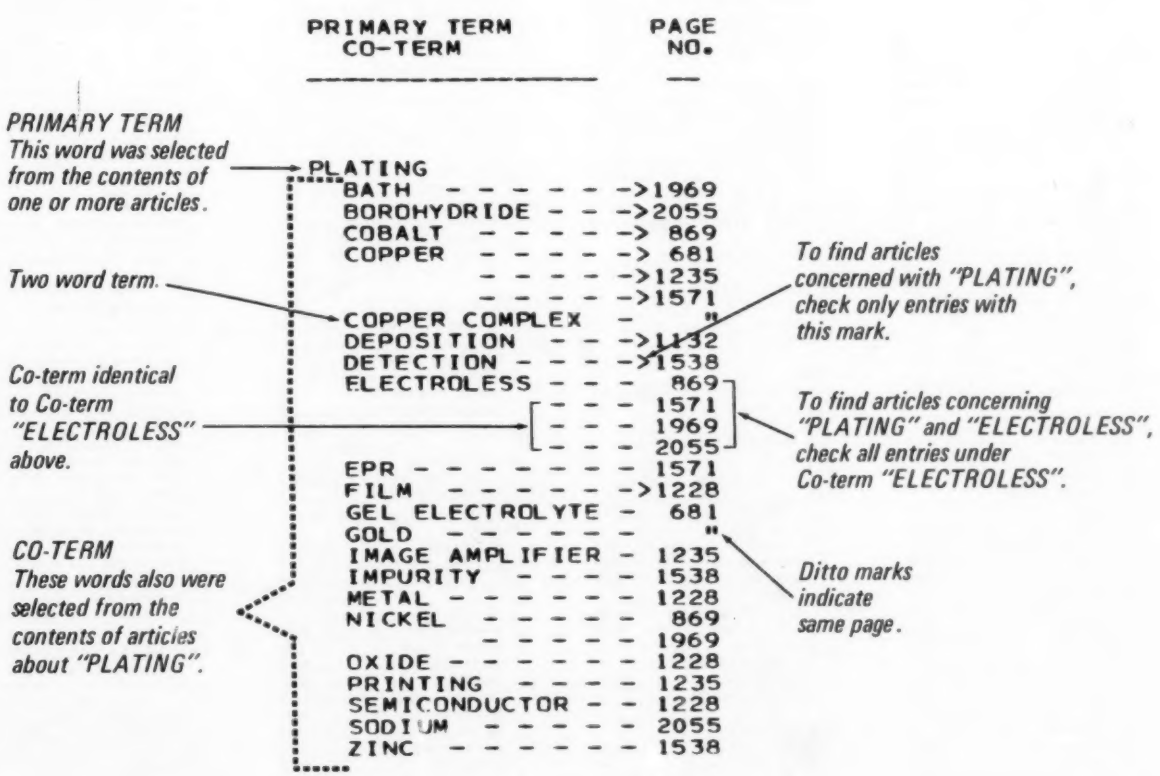
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